



迈拓电子
MAITUO ELECTRONIC

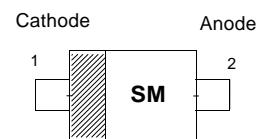
B16WS Plastic-Encapsulate Diodes



Schottky Barrier Diode

FEATURES

- Guard ring protection
- Low forward voltage drop
- For use in low voltage, high frequency inverters
- High surge current capability



SOD-323

Marking: SM

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RRM}	Maximum recurrent peak reverse voltage	60	V
V_{RMS}	Maximum RMS voltage	42	
V_{DC}	Maximum DC blocking voltage	60	
I_F	Continuous forward current	1	A
I_{FSM}	Non-repetitive Peak forward surge current@t=8.3ms	10	
P_{tot}	Total power dissipation	250	mW
$R_{\theta JA}$	Thermal resistance junction to ambient air	400	°C/W
T_J	Junction temperature	125	°C
T_{stg}	storage temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS(Ta=25°C unless otherwise specified)

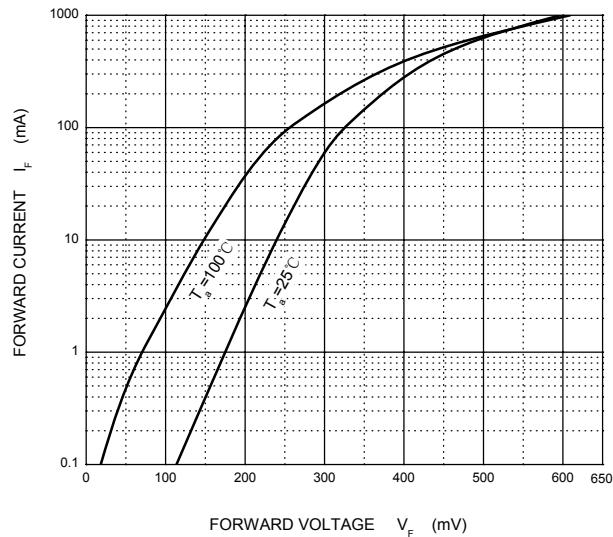
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Maximum instantaneous forward voltage	V_F	$I_F=1A$			0.7	V
Maximum DC reverse current at rated DC blocking voltage	I_R	$V_R=60V$			0.1	mA
Total capacitance	C_{tot}	$V_R=4V, f=1MHz$			120	pF



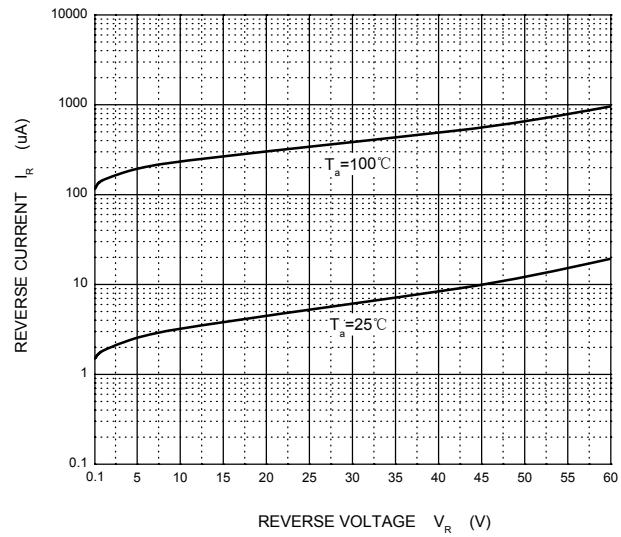
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Typical Characteristics

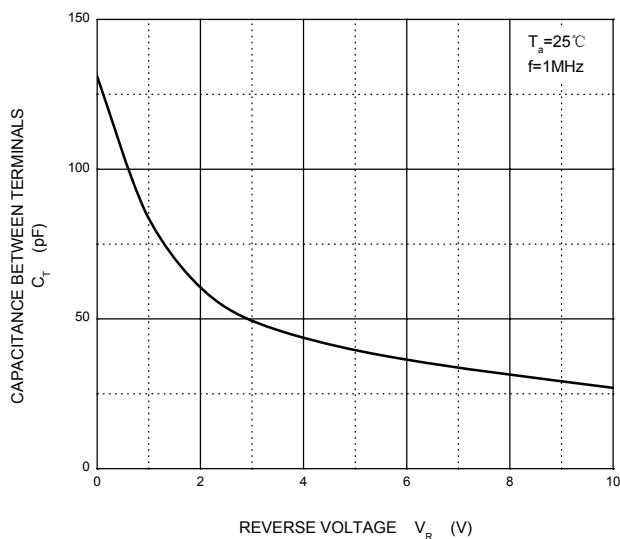
Forward Characteristics



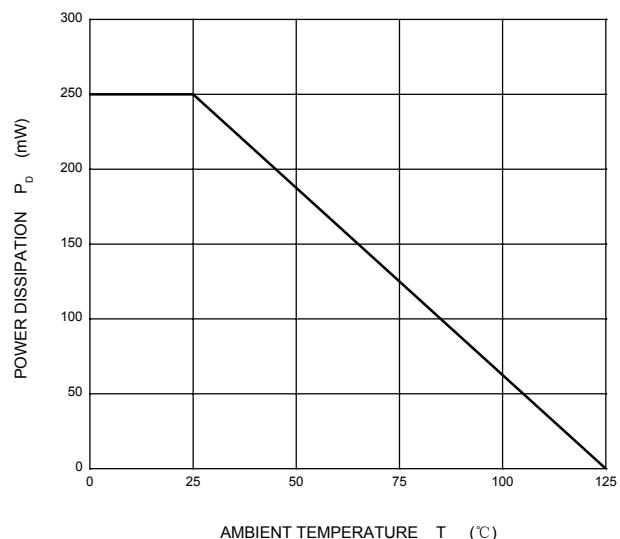
Reverse Characteristics



Capacitance Characteristics



Power Derating Curve





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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

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